PROCESS CPQ166

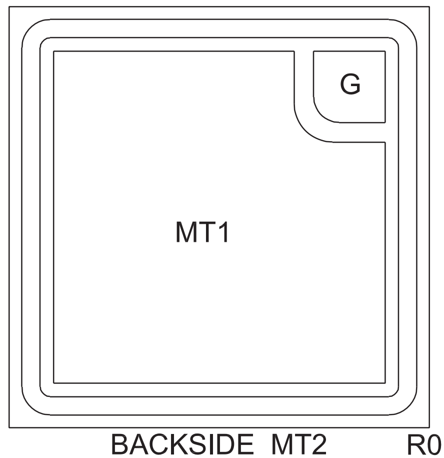
TRIAC

25 Amp, 600 Volt TRIAC Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	165 x 165 MILS
Die Thickness	9.1 MILS ± 0.4 MILS
MT1 Bonding Pad Area	134 x 100 MILS
Gate Bonding Pad Area	28 x 28 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



BACKSIDE MT2 R0

GROSS DIE PER 4 INCH WAFER

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PRINCIPAL DEVICE TYPES

CQDD-25M Series
CQ220-25M Series
CQ220-25MFP Series

R1 (29-April 2010)